

Appl. No. 09/902,277

CLAIMS

*Sub E17* 46  
33. A method of forming a bottom-gated thin film transistor comprising the following steps:

*full 124*  
forming a transistor gate;  
forming a polycrystalline thin film transistor layer over the transistor gate;  
forming a fluorine containing layer proximate the polycrystalline thin film transistor layer; and  
transferring fluorine into the polycrystalline thin film transistor layer from the fluorine containing layer.

*47* 46  
34. The method of claim 33 wherein the polycrystalline thin film transistor layer comprises silicon.

*48* 47 48  
35. The method of claim 33 wherein the forming a fluorine containing layer comprises forming a sacrificial fluorine containing layer over the thin film transistor layer by chemical vapor deposition utilizing WF<sub>6</sub> and SiH<sub>4</sub> precursors.

*Ruth 124* 49 48  
36. (Amended) The method of claim 35 further comprising, after the transferring fluorine, removing the sacrificial layer from over the thin film transistor layer.

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37. ) A method of forming a bottom-gated thin film transistor comprising

the following steps:

Reel 124  
forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine containing layer over the polycrystalline thin film  
transistor layer;

providing a buffering layer intermediate the thin film transistor layer and  
the fluorine containing layer; and

transferring fluorine into the polycrystalline thin film transistor layer from  
the fluorine containing layer.